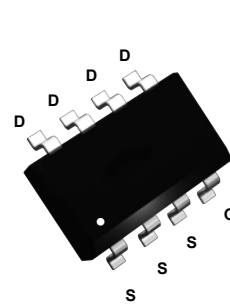
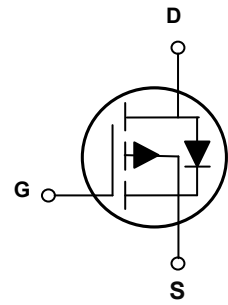


Main Product Characteristics

$V_{(BR)DSS}$	-30V
$R_{DS(ON)}$	25mΩ (Max.)
I_D	-8A



SOP-8



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFQ3025 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous ($T_C=25^\circ\text{C}$)	I_D	-8	A
Drain Current-Continuous ($T_C=100^\circ\text{C}$)		-5.6	
Drain Current-Pulsed ¹	I_{DM}	-64	A
Single Pulse Avalanche Energy ²	E_{AS}	95	mJ
Single Pulse Avalanche Current ²	I_{AS}	-19	A
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	3.2	W
Power Dissipation-Derate above 25°C		0.023	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	39	$^\circ\text{C/W}$
Operating Junction Temperature Range	T_J	-55 To +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 To +150	$^\circ\text{C}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-30	-	-	V
BV _{DSS} Temperature Coefficient	△BV _{DSS} /△T _J	Reference to 25°C, I _D =-1mA	-	-0.03	-	V/°C
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V, T _J =25°C	-	-	-1	μA
		V _{DS} =-24V, V _{GS} =0V, T _J =125°C	-	-	-100	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-7.5A	-	20	25	mΩ
		V _{GS} =-4.5V, I _D =-5A	-	32	39	
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =-250uA	-1.1	-1.7	-2.8	V
V _{GS(th)} Temperature Coefficient	△V _{GS(th)}		-	4	-	mV/°C
Forward Transconductance	gfs	V _{DS} =-5V, I _D =-5A	-	20	-	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{2,3}	Q _g	V _{DS} =-15V, I _D =-7.5A V _{GS} =-10V	-	21	-	nC
Gate-Source Charge ^{2, 3}	Q _{gs}		-	1.4	-	
Gate-Drain Charge ^{2, 3}	Q _{gd}		-	4.2	-	
Turn-On Delay Time ^{2, 3}	t _{d(on)}	V _{DD} =-15V, R _G =3Ω V _{GS} =-10V, I _D =-7.5A	-	12	-	nS
Rise Time ^{2, 3}	t _r		-	14	-	
Turn-Off Delay Time ^{2, 3}	t _{d(off)}		-	130	-	
Fall Time ^{2, 3}	t _f		-	95	-	
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, F=1MHz	-	1134	-	pF
Output Capacitance	C _{oss}		-	184	-	
Reverse Transfer Capacitance	C _{rss}		-	117	-	
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I _S	V _G =V _D =0V, Force Current	-	-	-8	A
Pulsed Source Current	I _{SM}		-	-	-64	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-3A, T _J =25°C	-	-	-1	V
Reverse Recovery Time	t _{rr}	I _F =-7A, di/dt=-100A/us	-	36	-8	ns
Reverse Recovery Charge	Q _{rr}		-	34	-64	nC

Notes:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2. $V_{DD}=-25V, V_{GS}=-10V, L=0.5mH, R_G=25\Omega$, starting $T_J=25^{\circ}\text{C}$.
3. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Typical Electrical and Thermal Characteristic Curves

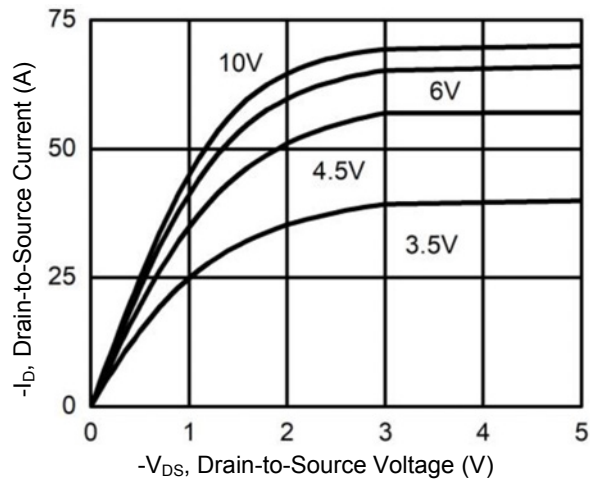


Figure 1. Output Characteristics

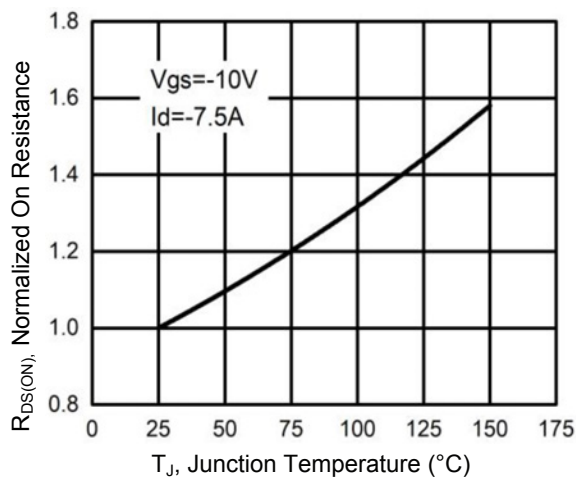


Figure 2. Normalized $R_{DS(ON)}$ vs. T_J

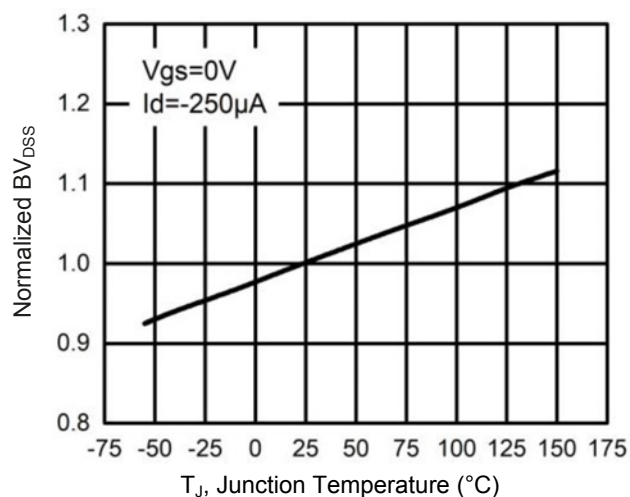


Figure 3. Normalized BV_{DS} vs. T_J

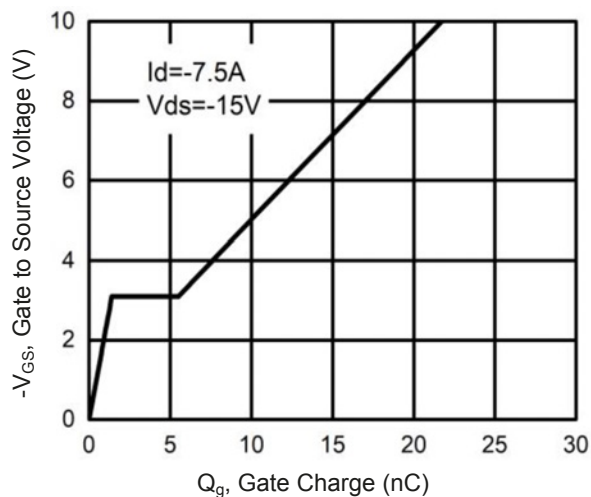


Figure 4. Gate Charge Waveform

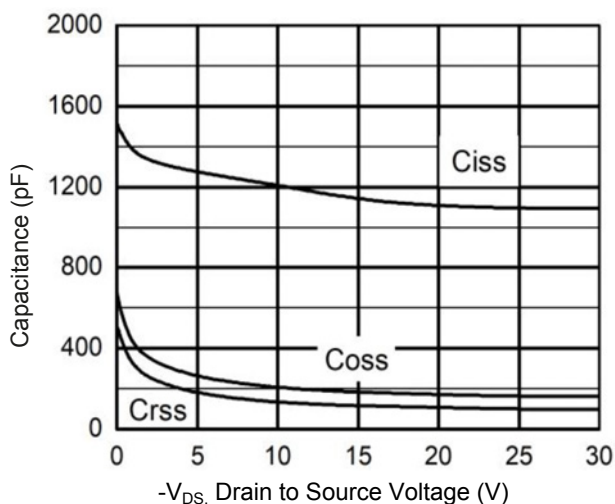


Figure 5. Capacitance Characteristics

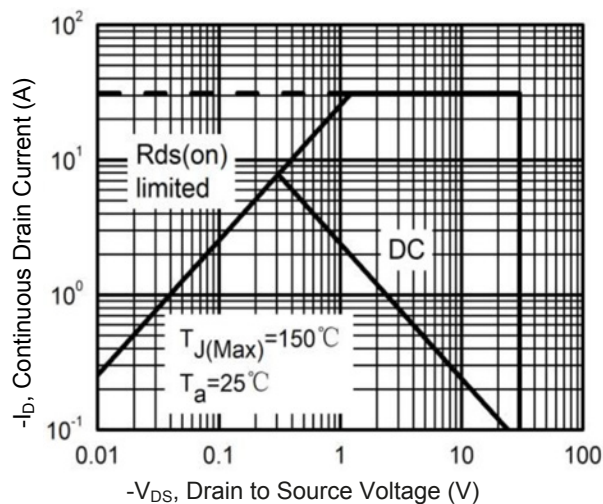
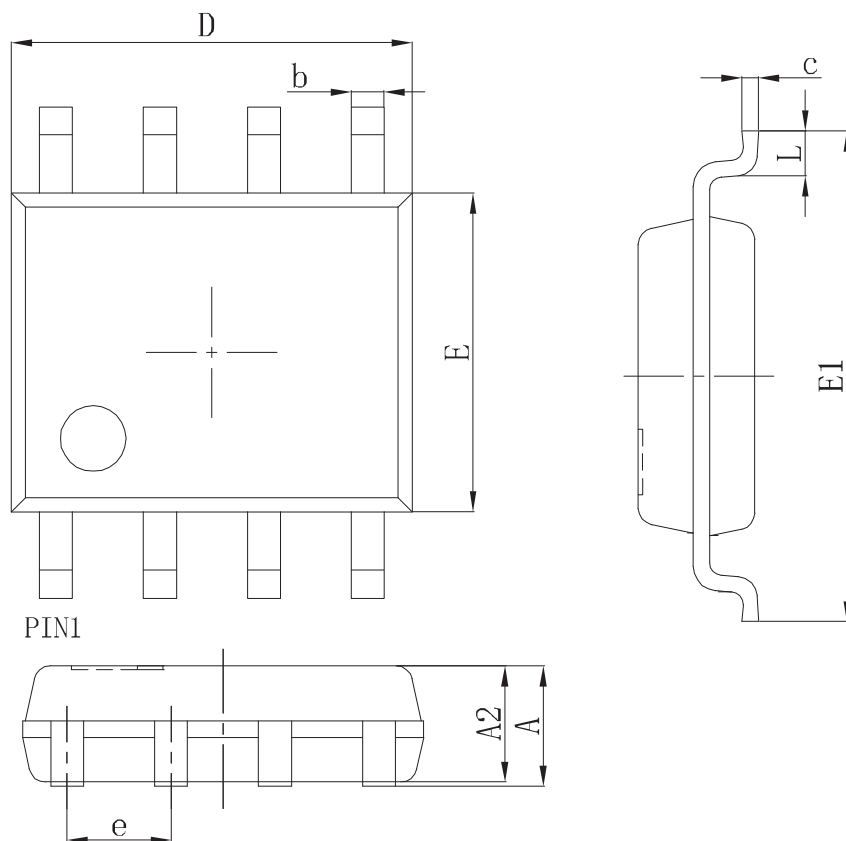


Figure 6. Safe Operation Area

Package Outline Dimensions (SOP-8)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.30	1.70	0.051	0.067
A2	1.25	1.55	0.049	0.061
c	0.17	0.25	0.007	0.010
E	3.80	4.00	0.150	0.157
E1	5.80	6.20	0.228	0.244
L	0.45	0.75	0.018	0.030
b	0.33	0.51	0.013	0.020
D	4.80	5.00	0.189	0.197
e	1.27 BSC		0.050 BSC	

Order Information

Device	Package	Marking	Packaging	SPQ
GSFQ3025	SOP-8	Q3025	Tape & Reel	3,000pcs / Reel